

SMPS MOSFET IRFPS40N50L

HEXFET® Power MOSFET

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- ZVS and High Frequency Circuit
- PWM Inverters

V_{DSS}	R_{DS(on)} typ.	I_D
500V	0.087Ω	46A

Benefits

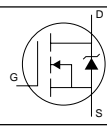
- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Low Trr and Soft Diode Recovery
- High Performance Optimised Anti-parallel Diode



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	46	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	29	
I _{DM}	Pulsed Drain Current ①	180	
P _D @ T _C = 25°C	Power Dissipation	540	W
	Linear Derating Factor	4.3	W/°C
V _{GS}	Gate-to-Source Voltage	± 30	V
	dv/dt Peak Diode Recovery dv/dt ③	25	V/ns
T _J	Operating Junction and	-55 to + 150	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	46	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	180		
V _{SD}	Diode Forward Voltage	—	—	1.5	V	T _J = 25°C, I _S = 46A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	170	250	ns	T _J = 25°C I _F = 46A
		—	220	330		T _J = 125°C di/dt = 100A/μs ④
Q _{rr}	Reverse Recovery Charge	—	705	1060	nC	T _J = 25°C
		—	1.3	2.0		T _J = 125°C
I _{RSM}	Reverse Recovery Current	—	9.0	—	A	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Typical SMPS Topologies

- Bridge Converters
- All Zero Voltage Switching

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.60	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ Ⓞ
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.087	0.100	Ω	$V_{GS} = 10V, I_D = 28A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	50	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	2.0	mA	$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	21	—	—	S	$V_{DS} = 50V, I_D = 46A$
Q_g	Total Gate Charge	—	—	380	nC	$I_D = 46A$
Q_{gs}	Gate-to-Source Charge	—	—	80		$V_{DS} = 400V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	190		$V_{GS} = 10V, \text{See Fig. 6 and 13}$ ④
$t_{d(on)}$	Turn-On Delay Time	—	27	—	ns	$V_{DD} = 250V$
t_r	Rise Time	—	170	—		$I_D = 46A$
$t_{d(off)}$	Turn-Off Delay Time	—	50	—		$R_G = 0.85\Omega$
t_f	Fall Time	—	69	—		$V_{GS} = 10V, \text{See Fig. 10}$ ④
C_{iss}	Input Capacitance	—	8110	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	960	—		$V_{DS} = 25V$
C_{riss}	Reverse Transfer Capacitance	—	130	—		$f = 1.0\text{MHz}, \text{See Fig. 5}$
C_{oss}	Output Capacitance	—	11200	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	240	—		$V_{GS} = 0V, V_{DS} = 400V, f = 1.0\text{MHz}$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	420	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$ ⑤

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	920	mJ
I_{AR}	Avalanche Current①	—	46	A
E_{AR}	Repetitive Avalanche Energy①	—	54	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.23	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient	—	40	

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.86\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 46A$ (See Figure 12a)
- ③ $I_{SD} \leq 46A$, $di/dt \leq 367A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.
- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

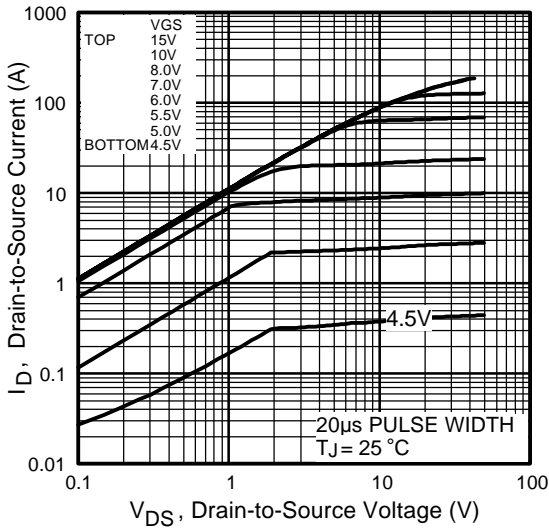


Fig 1. Typical Output Characteristics

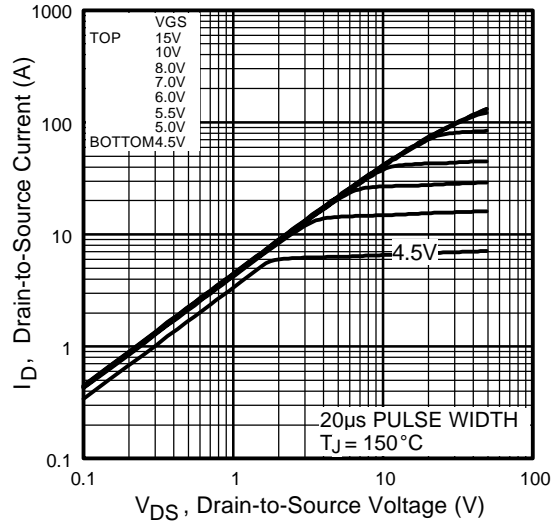


Fig 2. Typical Output Characteristics

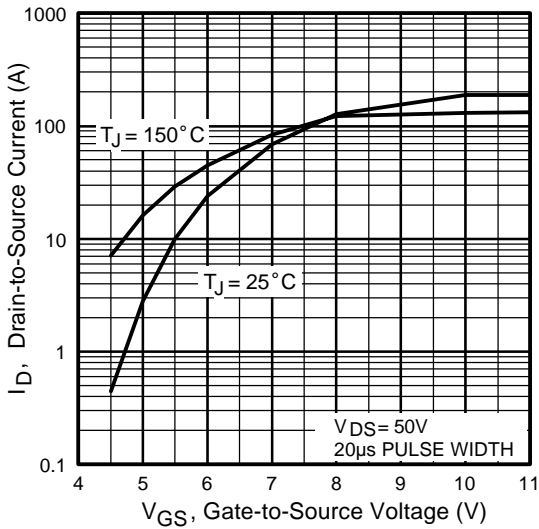


Fig 3. Typical Transfer Characteristics

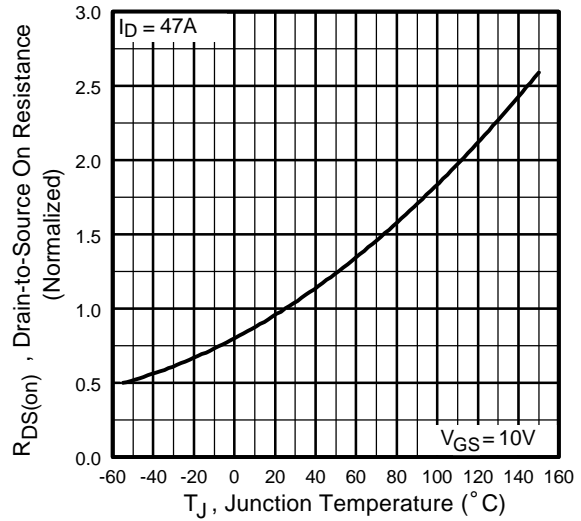


Fig 4. Normalized On-Resistance Vs. Temperature

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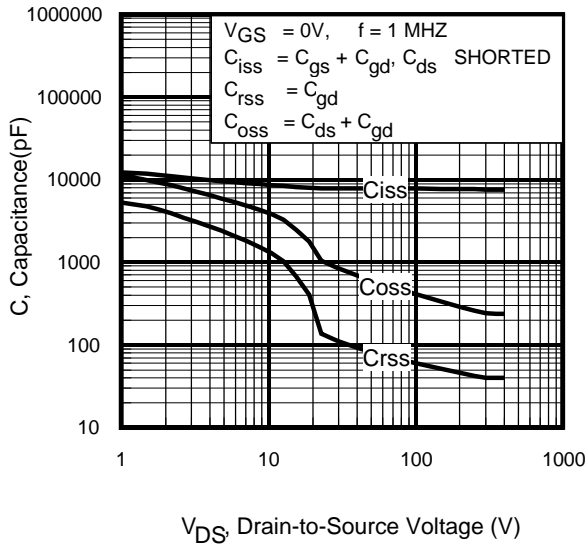


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

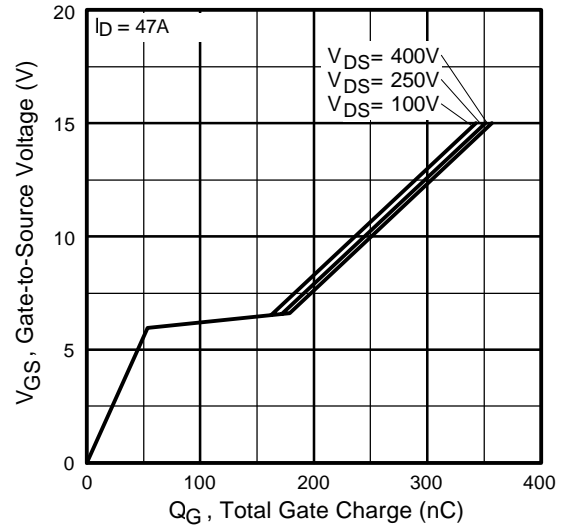


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

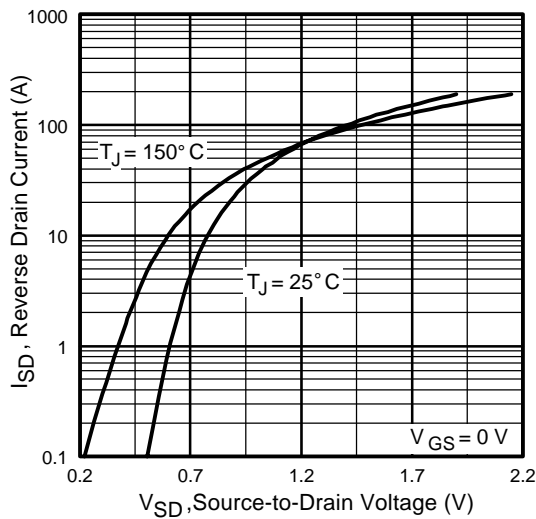


Fig 7. Typical Source-Drain Diode Forward Voltage

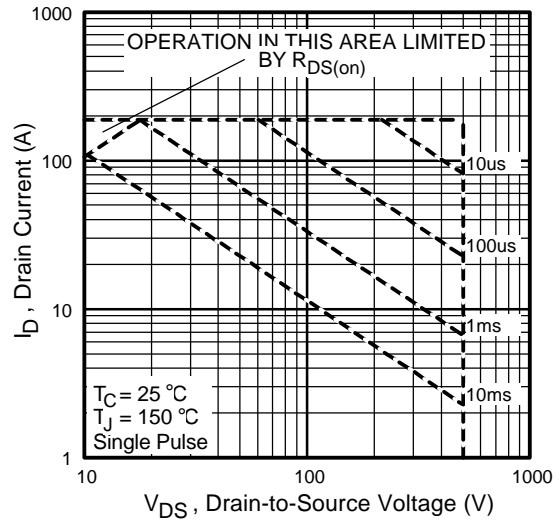


Fig 8. Maximum Safe Operating Area

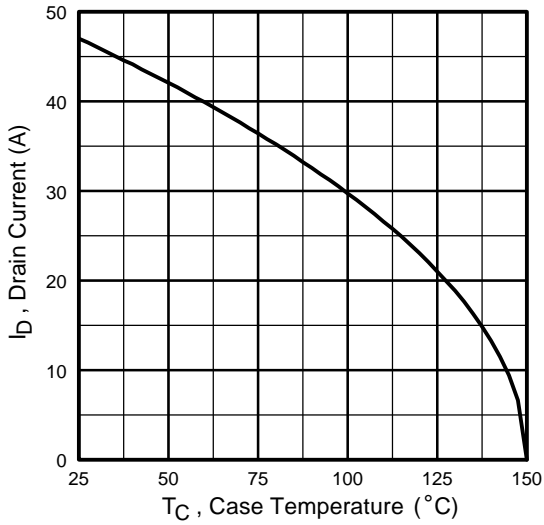


Fig 9. Maximum Drain Current Vs. Case Temperature

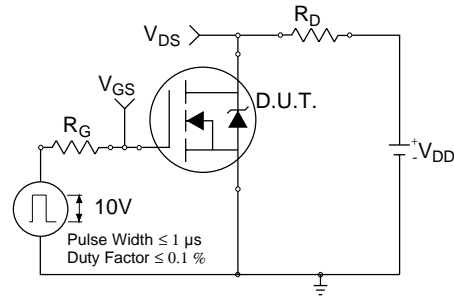


Fig 10a. Switching Time Test Circuit

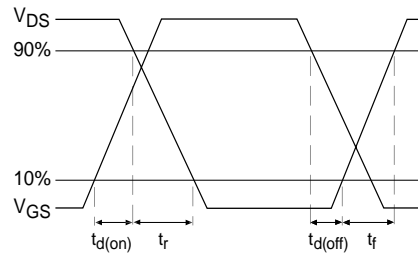


Fig 10b. Switching Time Waveforms

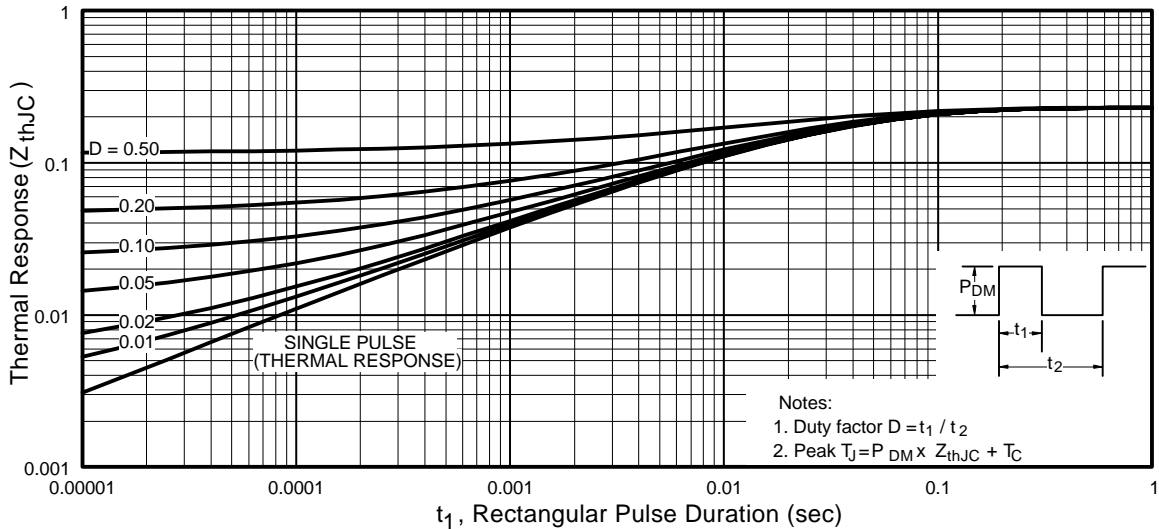


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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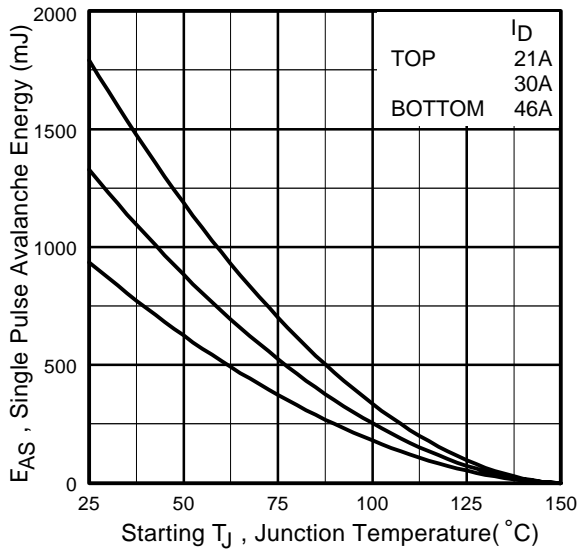


Fig 12a. Maximum Avalanche Energy Vs. Drain Current

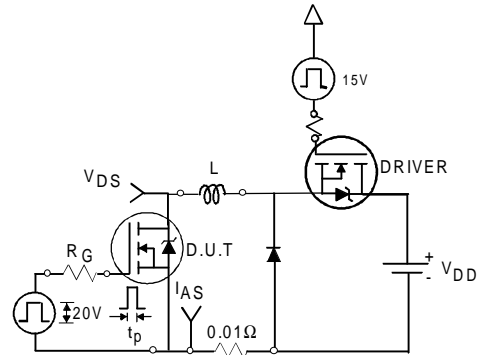


Fig 12c. Unclamped Inductive Test Circuit

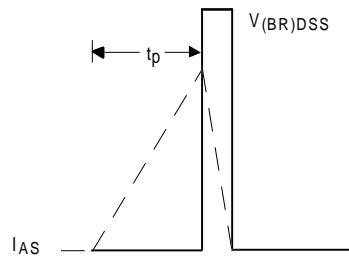


Fig 12d. Unclamped Inductive Waveforms

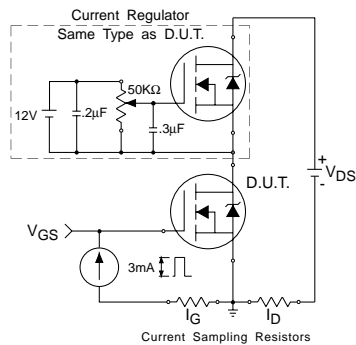


Fig 13a. Gate Charge Test Circuit

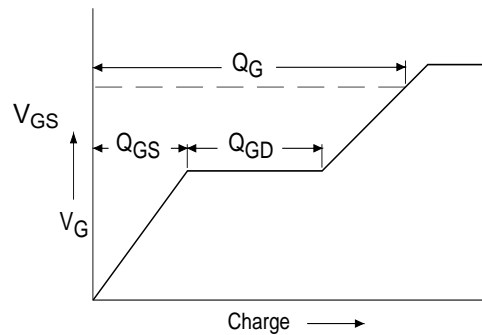
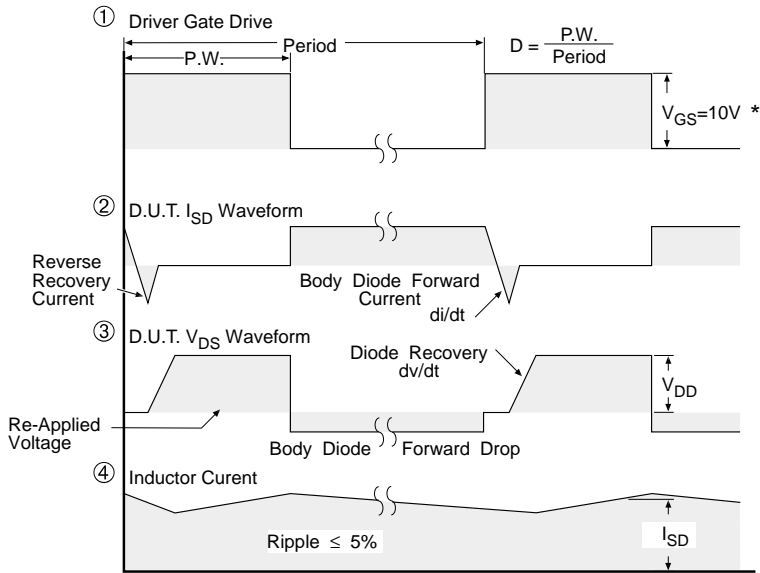
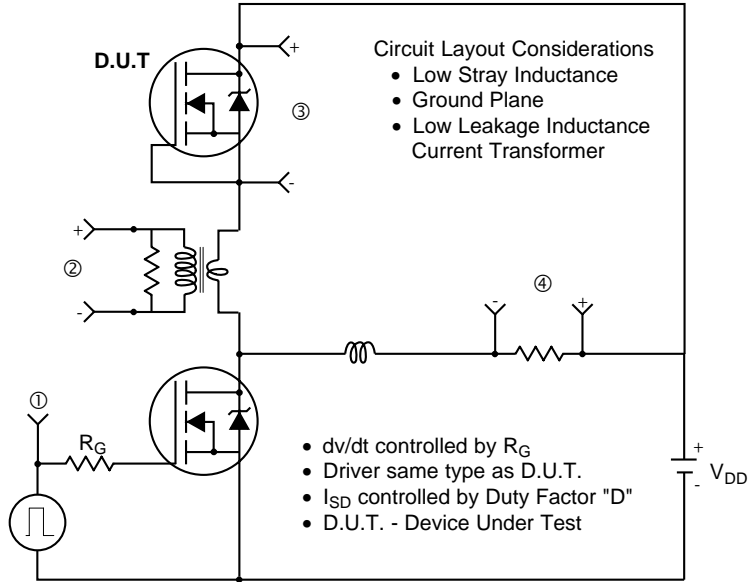


Fig 13b. Basic Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

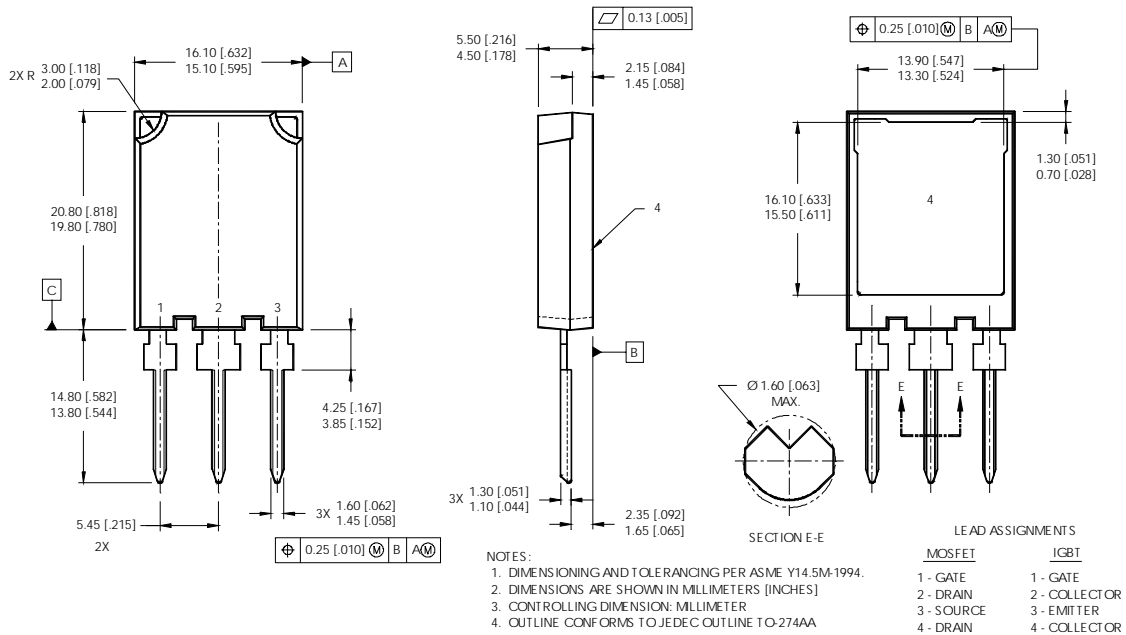
Fig 14. For N-Channel HEXFET® Power MOSFETs

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SUPER TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.
 This product has been designed and qualified for the industrial market.
 Qualification Standards can be found on IR's Web site.

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